



Description

The IRF7104PbF uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

$V_{DS} = -20V, I_D = -4A$

$R_{DS(ON)} < 95m\Omega @ V_{GS} = -4.5V$

$R_{DS(ON)} < 110m\Omega @ V_{GS} = -2.5V$

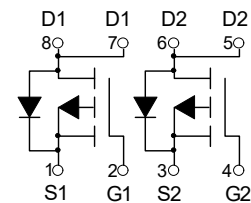
Application

PWM application

Load switch



SOP-8



Dual P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IRF7104PbF	SOP-8	HXY MOSFET	3000

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Drain Current-Continuous	-4	A
I_{DM}	Drain Current-Pulsed (Note 1)	-20	A
P_D	Maximum Power Dissipation	2.0	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	62.5	$^\circ C/W$



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.02	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-	5.8A-	85	95	mΩ
		V _{GS} =-2.5V, I _D =-3.5A	---	95	110	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.6	-1.1	-1.7	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	4.32	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-16V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-16V, V _{GS} =0V, T _J =55°C	---	---	-5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-3A	---	5.5	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	24	48	Ω
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-16V, V _{GS} =-4.5V, I _D =-5.8A	---	10.6	15	nC
Q _{gs}	Gate-Source Charge		---	1.0	---	
Q _{gd}	Gate-Drain Charge		---	2.0	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-15V, V _{GS} =-10V, R _G =6Ω I _D =-1A, R _G =10Ω	---	10	12	ns
T _r	Rise Time		---	4.9	6	
T _{d(off)}	Turn-Off Delay Time		---	22	42	
T _f	Fall Time		---	3	9	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	325	---	pF
C _{oss}	Output Capacitance		---	60	---	
C _{rss}	Reverse Transfer Capacitance		---	30	---	
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	-2.0	A
I _{SM}	Pulsed Source Current ^{2,4}		---	---	-20	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1.7A, T _J =25°C	---	---	-1	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper,t<10sec.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

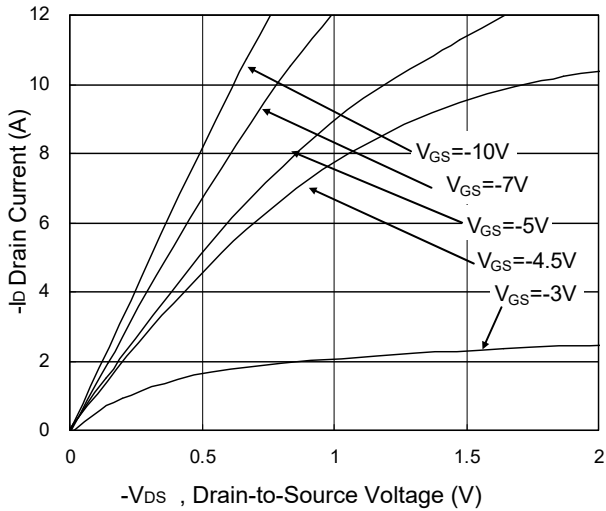


Fig.1 Typical Output Characteristics

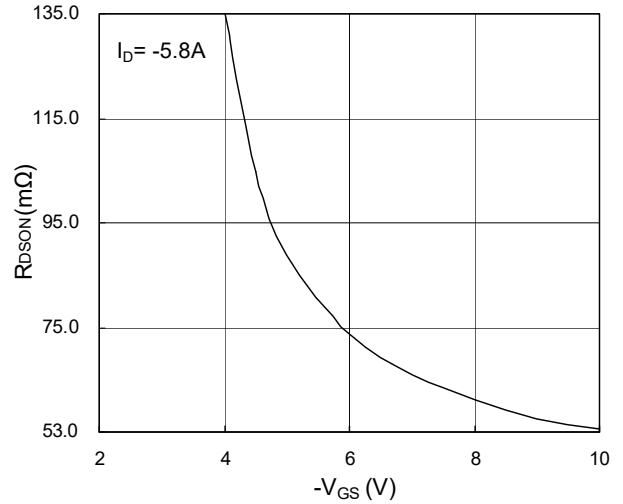


Fig.2 On-Resistance vs. G-S Voltage

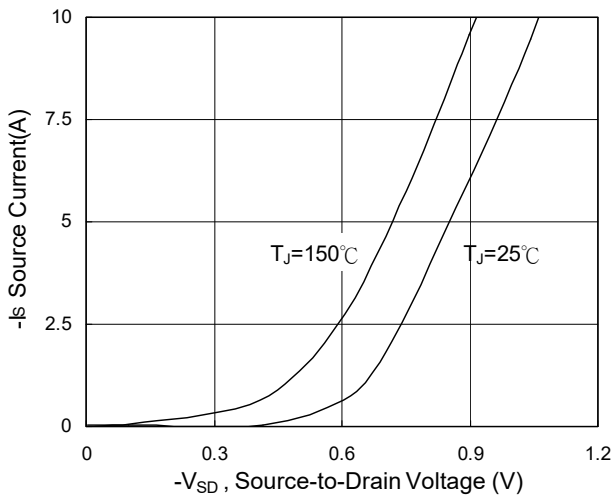


Fig.3 Forward Characteristics of Reverse

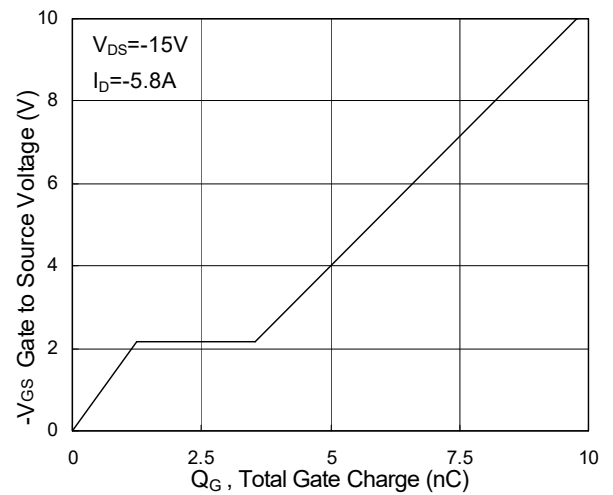


Fig.4 Gate-Charge Characteristics

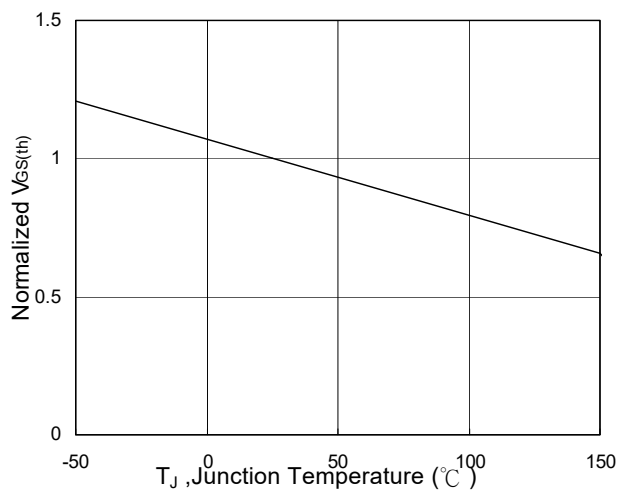


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

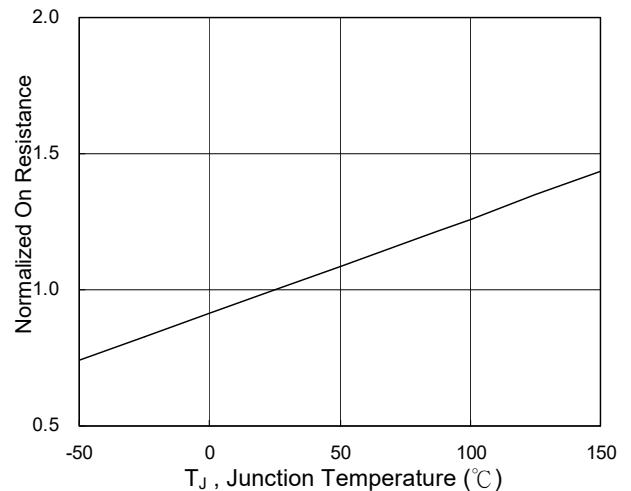


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

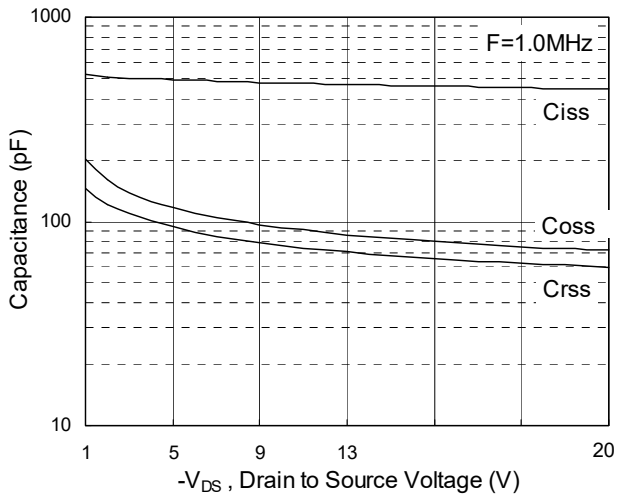


Fig.7 Capacitance

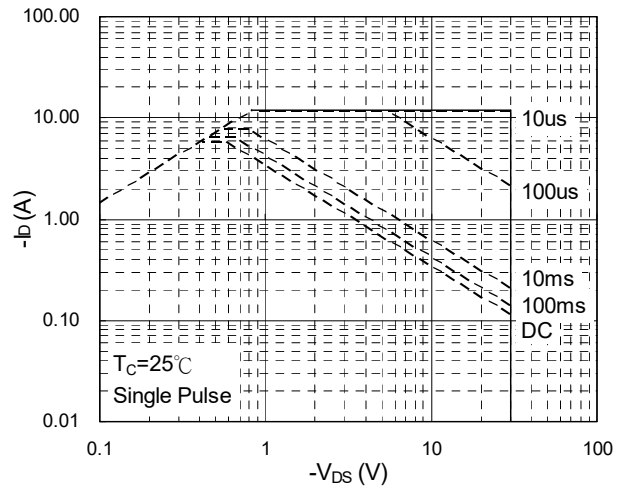


Fig.8 Safe Operating Area

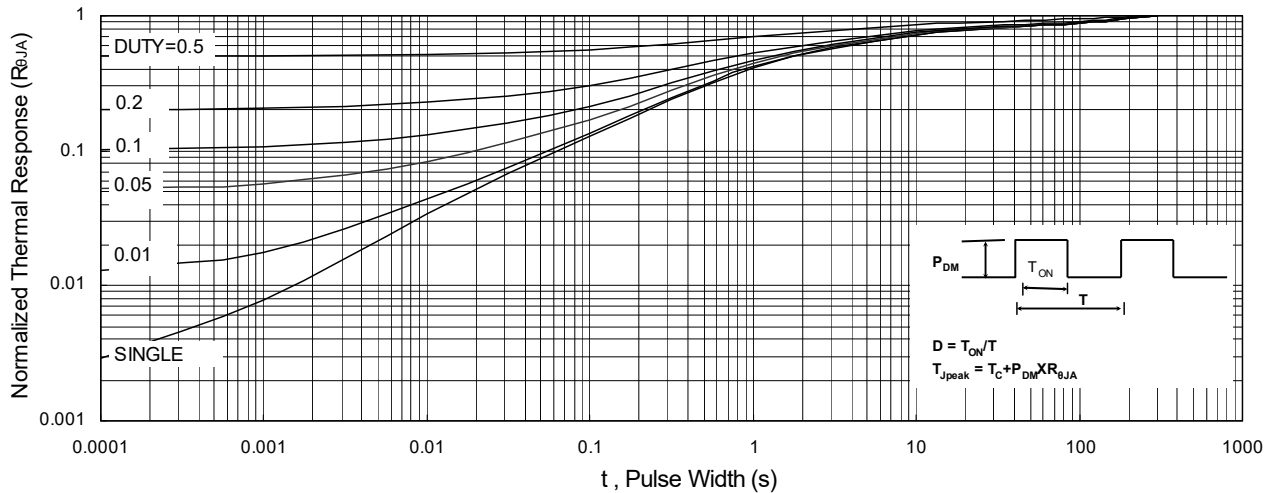


Fig.9 Normalized Maximum Transient Thermal Impedance

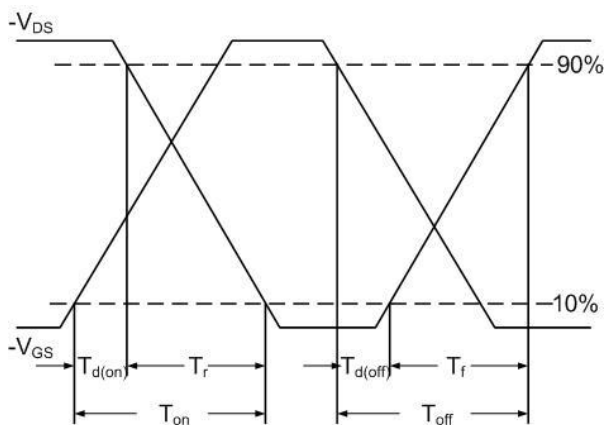


Fig.10 Switching Time Waveform

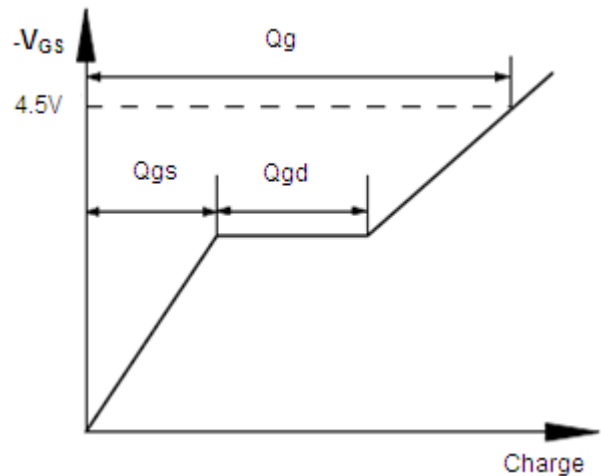
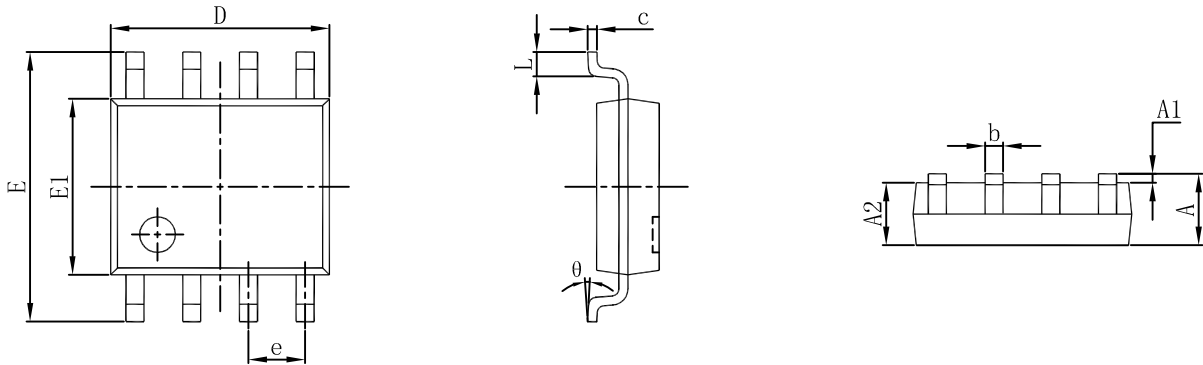


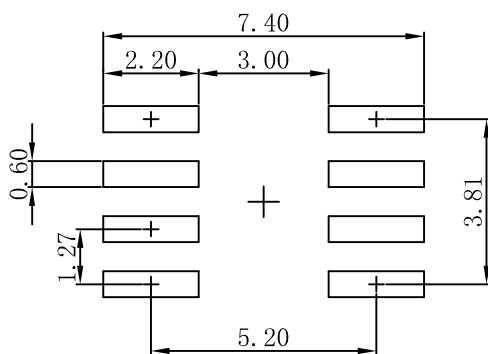
Fig.11 Gate Charge Waveform



SOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
theta	0°	8°	0°	8°



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.



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